

	<p>SIR410DP-T1-GE3</p>
	<p>Hersteller-Teilenummer: SIR410DP-T1-GE3</p>
	<p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p>
	<p>Teil der Beschreibung: MOSFET N-CH 20V 35A PPAK SO-8</p>
<p>Image may be representation. See specs for product details.</p>	<p>Datenblätter:  SIR410DP-T1-GE3.pdf</p>
	<p>RoHs Status: Bleifrei / RoHS-konform</p>
	<p>Lagerzustand: New original, 14969 pcs Stock Available.</p>
	<p>Liefern von: Hong Kong</p>
	<p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>

Spezifikationen

Teilenummer	SIR410DP-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 20V 35A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	14969 pcs Stock
Hersteller Standard Vorlaufzeit	27 Weeks
detaillierte Beschreibung	N-Channel 20V 35A (Tc) 4.2W (Ta), 36W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	4.2W (Ta), 36W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	35A (Tc)
Rds On (Max) @ Id, Vgs	4.8 mOhm @ 20A, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	41nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1600pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SIR410DP-T1-GE3-ND

SIR410DP-T1-GE3 ist neu im Original, Suche SIR410DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIR410DP-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIR410DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SIR408DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 25V 50A PPAK SO-8</p>	 <p>SIR412DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 25V 20A PPAK SO-8</p>	 <p>SIR412DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 25V 20A PPAK SO-8</p>	 <p>SiR412DP Vishay Precision Group SiR412DP VISHAY</p>
 <p>SIR414DP VB SIR414DP VB</p>	 <p>SIR410DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 20V 35A PPAK SO-8</p>	 <p>SiR410DP-T1-E3 VISHAY SIR410DP-T1-E3 VISHAY</p>	 <p>SiR412DP-T1-E3 Vishay Precision Group SiR412DP-T1-E3 VISHAY</p>

heiße Teile

Mehr

- | | | | | |
|-------------------|---------------------|--------------------|-------------------|-------------------|
| ⊛ SIR168DP-T1-GE3 | ➔ SIR172ADP-T1-GE3 | ➔ SIR172ADP-T1-GE3 | D SIR172DP | ➔ SIR172DP-T1-E3 |
| ⊠ SIR172DP-T1-GE3 | ⊛ SIR172DP-T1-GE3 | D SIR330DP-T1-GE3 | ➔ SIR330DP-T1-GE3 | ➔ SIR402DP-T1-GE3 |
| ⊛ SIR402DP-T1-GE3 | ⊠ SIR403EDP-T1-GE3 | ⊛ SIR403EDP-T1-GE3 | ➔ SIR404DP | ➔ SiR404DP-T1-E3 |
| D SIR404DP-T1-GE3 | ⊛ SIR404DP-T1-GE3 | ⊠ SIR406DP | ⊛ SIR406DP-T1-E3 | ➔ SIR406DP-T1-GE3 |
| ➔ SIR406DP-T1-GE3 | ➔ SIR406DP-T1-GE3-S | ⊛ SIR408DP-T1-GE3 | ⊠ SIR408DP-T1-GE3 | ➔ SiR410DP-T1-E3 |
| ➔ SIR410DP-T1-GE3 | ➔ SiR412DP | D SiR412DP-T1-E3 | ⊛ SIR412DP-T1-GE3 | ⊠ SIR412DP-T1-GE3 |
| ⊛ SIR414DP | D SIR414DP-T1-GE3 | ➔ SIR414DP-T1-GE3 | ➔ SIR416DP | ➔ SiR416DP-T1-E3 |
| ⊠ SIR416DP-T1-GE3 | ⊛ SIR416DP-T1-GE3 | ➔ SiR418DP-T1-E3 | ➔ SIR418DP-T1-GE3 | ➔ SIR418DP-T1-GE3 |
| ⊛ SiR422DP-T1-E3 | ⊠ SIR422DP-T1-GE3 | ⊛ SIR422DP-T1-GE3 | D SIR424DP-T1-GE3 | ➔ SIR424DP-T1-GE3 |
| ➔ SIR426DP-T1-GE3 | ⊛ SIR426DP-T1-GE3 | ⊠ SIR428DP | ⊛ SIR428DP-T1-E3 | ➔ SIR428DP-T1-GE3 |

Contact us:Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited

